

**NON-VOLATILE MEMORY AND METHOD  
WITH REDUCED NEIGHBORING CHARGE COUPLING ERRORS**

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**ABSTRACT OF THE DISCLOSURE**

When programming a contiguous page of memory storage units, every time a memory storage unit has reached its targeted state and is program-inhibited or locked out from further programming, it creates a perturbation on an adjacent memory storage unit still under programming. The present invention provides as part of a programming circuit and method in which an offset to the perturbation is added to the adjacent memory storage unit still under programming. The offset is added by a controlled coupling between the adjacent bit lines of the program-inhibited memory storage unit and the still under programming memory storage unit. In this way, an error inherent in programming in parallel high-density memory storage units is eliminated or minimized.